RHP030N03

4V Drive Nch MOSFET

Data Sheet

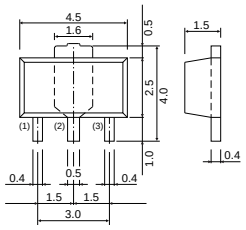
●Structure
Silicon N-channel MOSFET

●Features
1) Low On-resistance.
2) 4V drive.

●Applications
Switching

●Dimensions (Unit : mm)

MPT3
SOT-89



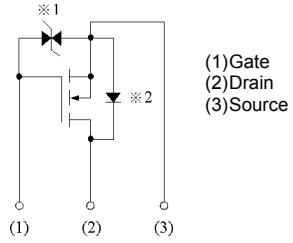
(1)Gate
(2)Drain
(3)Source

Abbreviated symbol : KZ

●Packaging specifications

Type	Package	Taping
	Code	T100
	Basic ordering unit (pieces)	1000
RHP030N03		○

●Inner circuit



(1)Gate
(2)Drain
(3)Source

※1 ESD PROTECTION DIODE
※2 BODY DIODE

●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	30	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	Continuous	I_D	3	A
	Pulsed	I_{DP} *1	10	A
Reverse drain current	Continuous	I_{DR}	3	A
	Pulsed	I_{DRP} *1	10	A
Total power dissipation		P_D	500	mW
			2 *2	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	−55 to +150	°C

*1 Pw≤10μs, Duty cycle≤1%
*2 When mounted on a 40×40×0.7mm ceramic board

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)	250	°C/W
		62.5 *	°C/W

* When mounted on a 40×40×0.7mm ceramic board

●**Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	±10	μA	V_{GS}=±20V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)\ DSS}$	30	–	–	V	I_D= 1mA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	–	–	1	μA	V_{DS}= 30V, V_{GS}=0V
Gate threshold voltage	$V_{GS\ (th)}$	1.0	–	2.5	V	V_{DS}= 10V, I_D= 1mA
Static drain-source on-state resistance	$R_{DS\ (on)}$*	–	90	120	mΩ	I_D= 3A, V_{GS}= 10V
		–	160	210	mΩ	I_D= 3A, V_{GS}= 4V
Forward transfer admittance	$\|Y_{fs}\|$ *	2.0	–	–	S	V_{DS}= 10V, I_D= 3A
Input capacitance	C_{iss}	–	160	–	pF	V_{DS}= 10V
Output capacitance	C_{oss}	–	90	–	pF	V_{GS}=0V
Reverse transfer capacitance	C_{rss}	–	27	–	pF	f=1MHz
Turn-on delay time	$t_{d\ (on)}$ *	–	7	–	ns	V_{DD}≒ 15V I_D= 1.5A V_{GS}= 10V R_L=10Ω R_G=10Ω
Rise time	t_r *	–	11	–	ns	
Turn-off delay time	$t_{d\ (off)}$ *	–	15	–	ns	
Fall time	t_f *	–	4.5	–	ns	
Total gate charge	Q_g *	–	6.5	–	nC	V_{DD}≒15V
Gate-source charge	Q_{gs} *	–	1.0	–	nC	V_{GS}= 10V
Gate-drain charge	Q_{gd} *	–	1.5	–	nC	I_D= 3A

*Pulsed

●Electrical characteristics curves

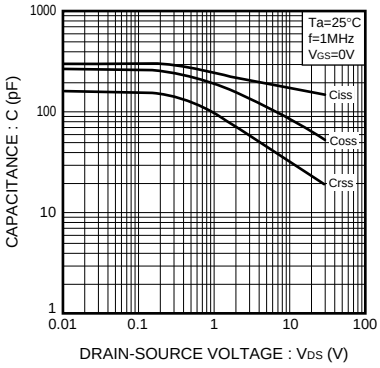


Fig.1 Typical Capacitance vs. Drain-Source Voltage

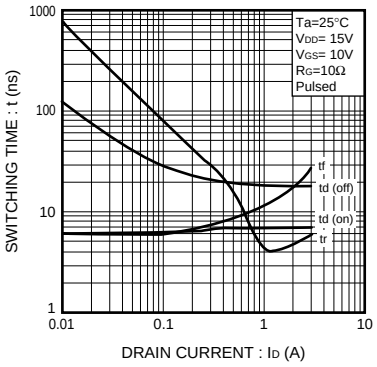


Fig.2 Switching Characteristics

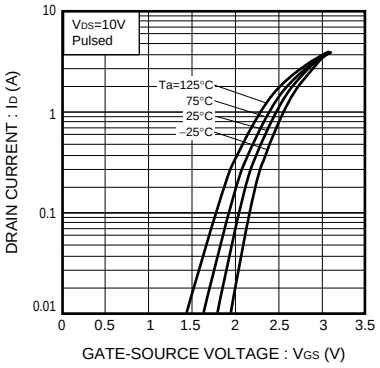


Fig.3 Typical Transfer Characteristics

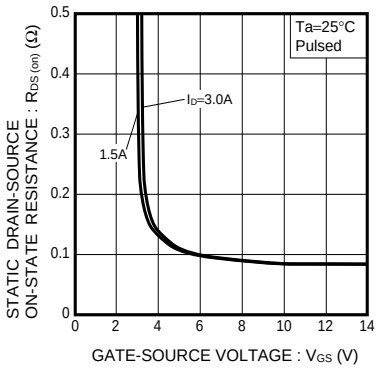


Fig.4 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

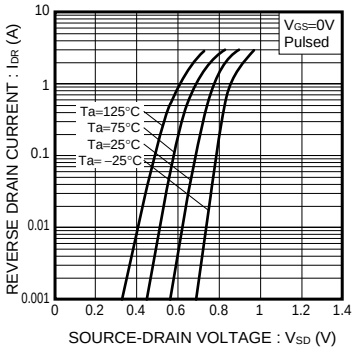


Fig.5 Reverse Drain Current vs. Source-Drain Voltage (I)

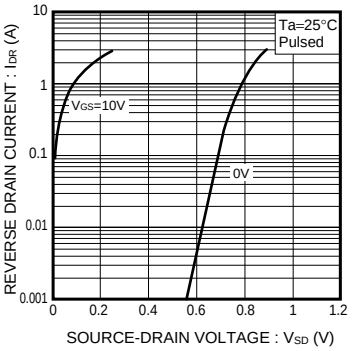


Fig.6 Reverse Drain Current vs. Source-Drain Voltage (II)

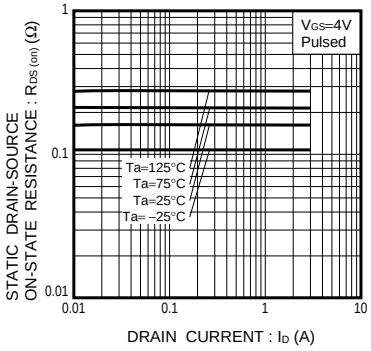


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current (II)

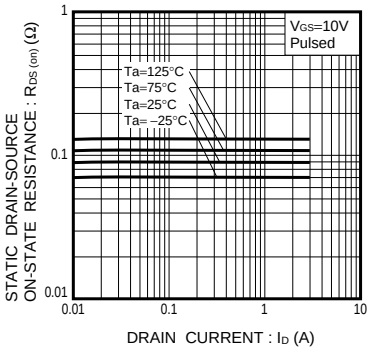


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current (I)

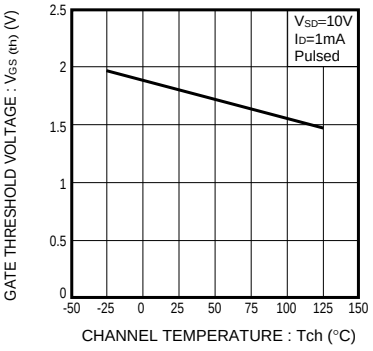


Fig.9 Gate Threshold Voltage vs. Channel Temperature

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